



New Product

TP0610K
Vishay Siliconix

P-Channel 60-V (D-S) MOSFET

TrenchFET[®]
MOSFETs

PRODUCT SUMMARY			
V _{(BR)DSS(min)} (V)	r _{DS(on)} (Ω)	V _{GS(th)} (V)	I _D (mA)
-60	6 @ V _{GS} = -10 V	-1 to -3.0	-185



ESD Protected
2000 V

FEATURES

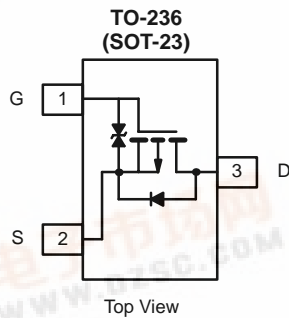
- High-Side Switching
- Low On-Resistance: 6 Ω
- Low Threshold: -2 V (typ)
- Fast Switching Speed: 20 ns (typ)
- Low Input Capacitance: 20 pF (typ)
- Gate-Source ESD Protection

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven Without Buffer

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid State Relays



Marking Code: 6Kw//
6K = Part Number Code for TP0610K
w = Week Code
// = Lot Traceability

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current ^a	I _D	T _A = 25 °C	-185
		T _A = 100 °C	-115
Pulse Drain Current ^b	I _{DM}	-800	mA
Power Dissipation ^a	P _D	T _A = 25 °C	350
		T _A = 100 °C	140
Maximum Junction-to-Ambient ^a	R _{thJA}	350	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C

Notes:
a. Surface mounted on FR4 board.
b. Pulse width limited by maximum junction temperature.

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SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -10 μA	-60			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1		-3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±10	μA
		V _{DS} = 0 V, V _{GS} = ±10 V			±200	nA
		V _{DS} = 0 V, V _{GS} = ±10 V, T _J = 85 °C			±500	
		V _{DS} = 0 V, V _{GS} = ±5 V			±100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -50 V, V _{GS} = 0 V			-25	nA
		V _{DS} = -50 V, V _{GS} = 0 V, T _J = 85 °C			-250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -10 V, V _{GS} = -4.5 V	-50			mA
		V _{DS} = -10 V, V _{GS} = -10 V	-600			
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -25 mA			10	Ω
		V _{GS} = -10 V, I _D = -500 mA			6	
		V _{GS} = -10 V, I _D = -500 mA, T _J = 125 °C			9	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -100 mA	80			mS
Diode Forward Voltage ^a	V _{SD}	I _S = -200 mA, V _{GS} = 0 V			-1.4	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} = -30 V, V _{GS} = -15 V, I _D ≅ -500 mA		1.7		nC
Gate-Source Charge	Q _{gs}			0.26		
Gate-Drain Charge	Q _{gd}			0.46		
Input Capacitance	C _{iss}	V _{DS} = -25 V, V _{GS} = 0 V, f = 1 MHz		23		pF
Output Capacitance	C _{oss}			10		
Reverse Transfer Capacitance	C _{rss}			5		
Switching^b						
Turn-On Time	t _{ON}	V _{DD} = -25 V, R _L = 150 Ω I _D ≅ -200 mA, V _{GEN} = -10 V R _G = 10 Ω		20		ns
Turn-Off Time	t _{OFF}			35		

Notes

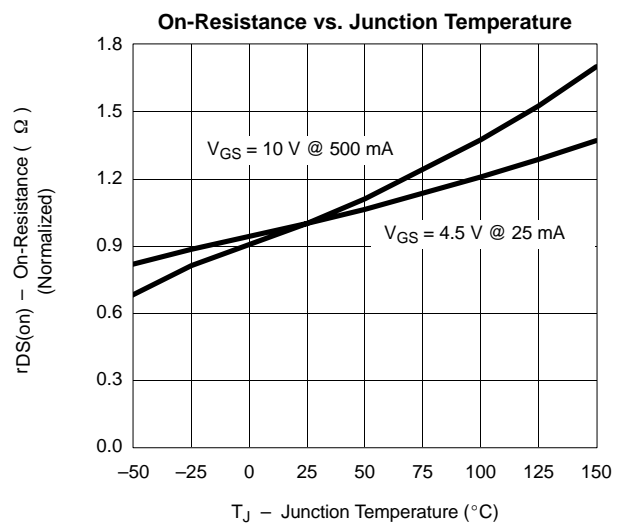
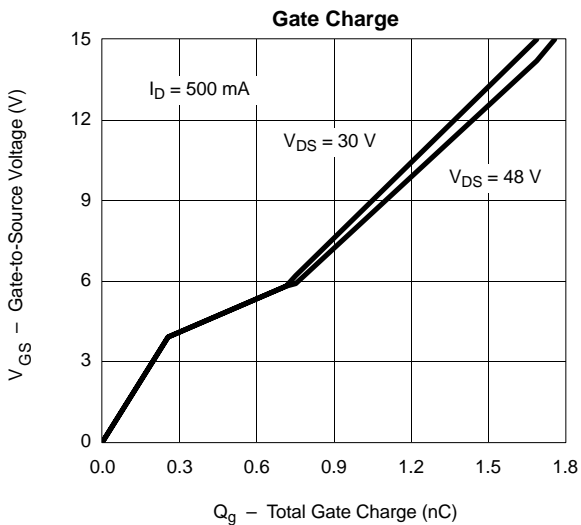
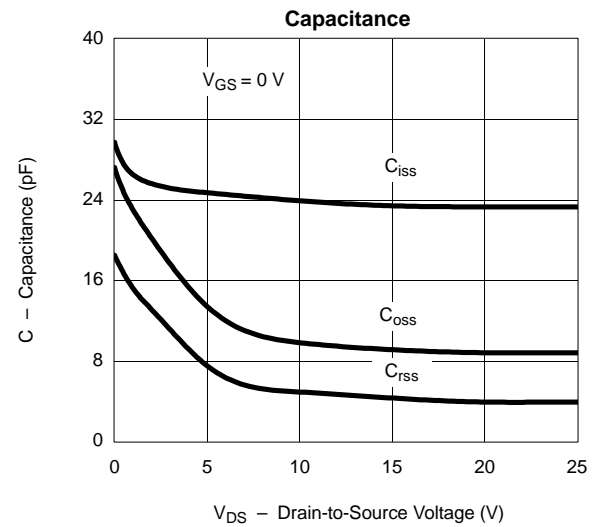
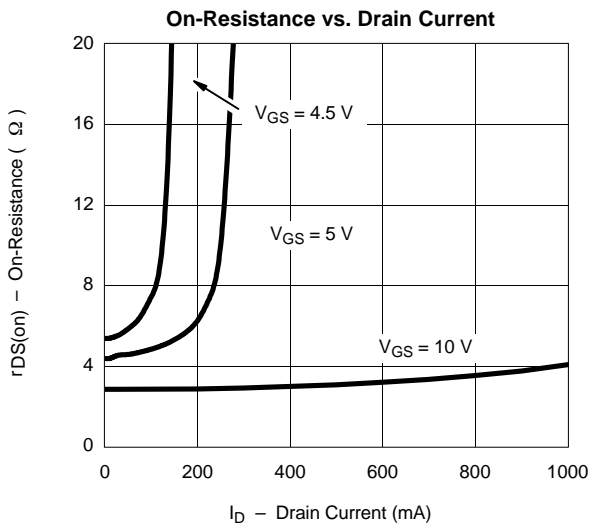
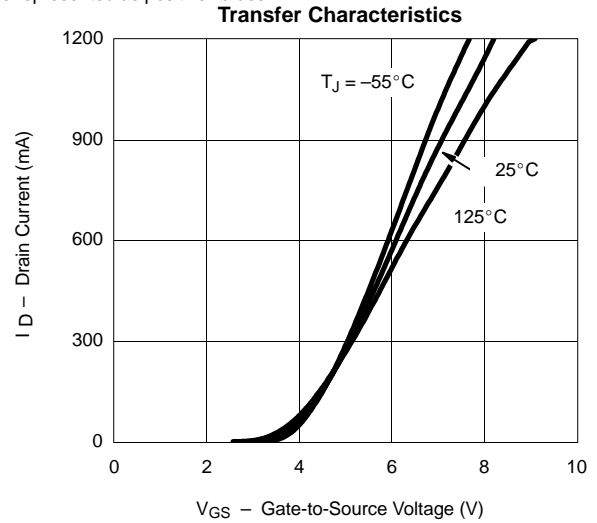
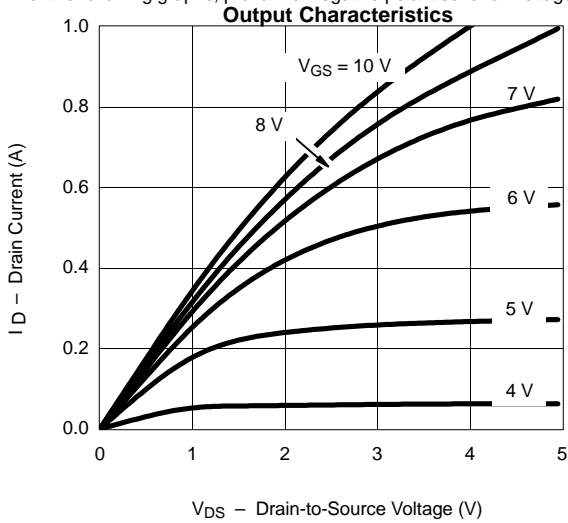
- a. Pulse test: PW ≤ 300 ms duty cycle ≤ 2%.
- b. Switching time is essentially independent of operating temperature.

TPJO60



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.





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